

Figure 1. Growth rate at different temperatures with a rotation speed of 12 rpm which is equivalent to 0.63 sec of DIPAS pulse, 2.08 sec of purge, 1.0 sec of NH₃ plasma and 1.30 sec of post purge.

Figure 3. Wet etch rate in diluted HF of films deposited at different temperatures.

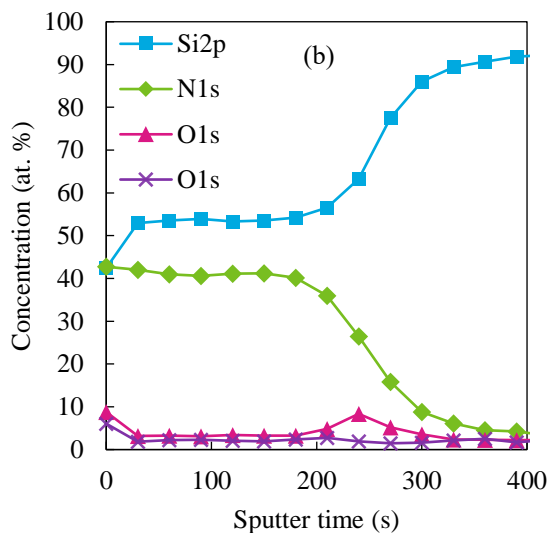
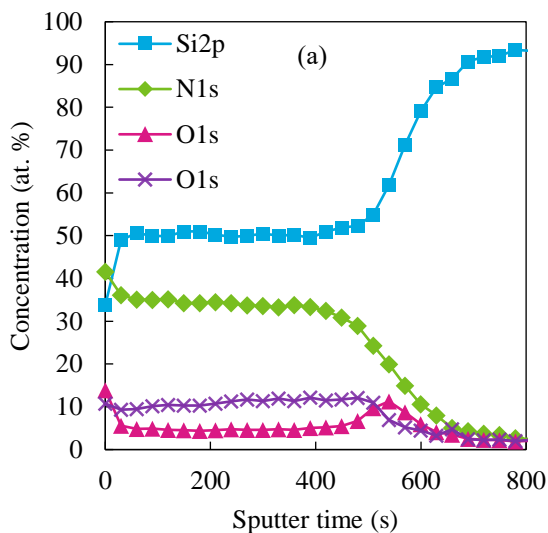


Figure 2. X-ray photoelectron spectroscopy (XPS) depth profiles for films deposited at (a) 100°C and (b) 350°C.

References

- [1] Meng, Xin, et al., *Materials* 9.12 (2016): 1007.
- [2] Profijt, H. B., et al., *Journal of Vacuum Science & Technology A: Vacuum, Surfaces, and Films* 29.5 (2011): 050801.
- [3] Knoops, Harm CM, et al., *ACS applied materials & interfaces* 7.35 (2015): 19857-19862.
- [4] Provine, J., et al., *AIP Advances* 6.6 (2016): 065012.
- [5] Triyoso, Dina H., et al., *ECS Journal of Solid State Science and Technology* 2.11 (2013): N222-N227.
- [6] Ande, Chaitanya Krishna, et al., *The journal of physical chemistry letters* 6.18 (2015): 3610-3611.